SURFACE MOUNT SCHOTTKY BARRIER RECTIFIERS

Reverse Voltage - 20 to 40 V Forward Current - 1 A

Features

- Plastic package has Underwriters Laboratory Classification 94V-0
- Metal silicon junction, majority carrier conduction
- For surface mount applications
- Guard ring for overvoltage protection
- Low power loss, high efficiency
- High current capability, Low forward voltage drop
- High surge capability

SMA (DO-214AC) 0.067(1.7)0.110(2.80) 0.086(2.18) 0.183(4.65) 0.157(3.99) 0.012(0.305) 0.096(2.42) 0.067(1.70) 0.060(1.52) 0.030(0.76) 0.008(0.203)Max. 0.209(5.31)

Dimensions in inches and (millimeters)

Mechanical Data

• Case: SMA (DO-214AC) molded plastic case • Terminals: Solder plate, solderable per

MIL-STD -750, method 2026

• Polarity: Color band denotes cathode end

• Mounting Position: Any

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, resistive or inductive load, for capacitive load, derate by 20%

capacitive load, derate by 20%		1			1	
Parameter		Symbols	SS5817	SS5818	SS5819	Units
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	20	30	40	V
Maximum RMS Voltage		V_{RMS}	14	21	28	V
Maximum DC Blocking Voltage		V_{DC}	20	30	40	V
Maximum Average Forward Rectified Current 0.375" (9.5 mm) Load Length at $T_L = 90$ °C		I _(AV)	1			А
Peak Forward Surge Current 8.3mS Single Half Sine-wave Superimposed on Rated Load (JEDEC Method) at $T_L = 70$ °C		I _{FSM}	25			Α
Maximum Instantaneous Forward Voltage at 1 A		V_{F}	0.45	0.55	0.6	V
Maximum Instantaneous Reverse Current at Rated	at T _A = 25°C	- I _R	0.5			mA
DC Blocking Voltage	at T _A =100 °C		10			mA
Typical Junction Capacitance 1)		CJ	110			pF
Typical Thermal Resistance ²⁾		$R_{\theta JA}$	88			°C/W
Operating and Storage Temperature Range		T _J ,T _S	- 65 to + 125			°C

¹⁾ Measured at 1 MHz and reverse voltage of 4 volts.













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²⁾ Thermal Resistance (from Junction to Ambient) Vertical P.C.B Mounted, with 1.5 X 1.5" (38 X 38 mm) copper pads.

FIG.1-FORWARD CURRENT DERATING CURVE

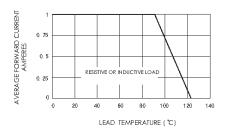


FIG.3-TYPICAL INSTANTANEOUS FORWARD **CHARACTERISTICS**

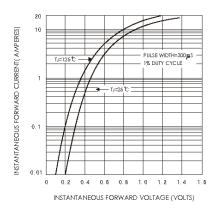


FIG.5-TYPICAL JUNCTION CAPACITANCE

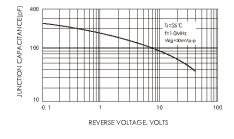


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

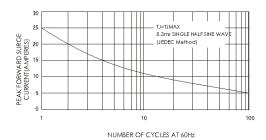


FIG.4-TYPICAL REVERSE CHARACTERISTICS

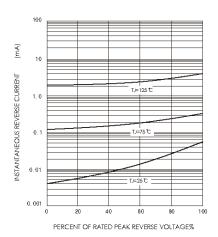
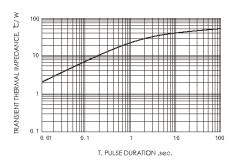


FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE





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